

FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT		ATTY DOCKET NO. 536-009.028	SERIAL NO. To be assigned 10/581127
		APPLICANT: B. HEINEMANN et al.	
		FILING DATE: Herewith	ART UNIT: To be assigned

UNITED STATES PATENT DOCUMENTS

EXAM. INITIAL	DOCUMENT NUMBER	DATE	INVENTOR/ASSIGNEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	2005/0023642	Feb. 03, 2005	Heinemann et al.			
	2003/0146477	Aug. 07, 2003	Krutsick			
	2003/0146468	Aug. 07, 2003	Gris et al.			
	2002/0168829	Nov. 14, 2002	Bock et al.			
	2003/0162360	Aug. 28, 2003	Beasom			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO
	EP 0 746 038	Dec. 19, 2001	EP			
	2000188296	July 04, 2000	JP			
	2000269350	Sept. 29, 2000	JP			

OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

1	M. C. Wilson et al., "Process HJ: A 30 GHz NPN and 20 GHz PNP complementary bipolar process for high linearity RF circuits," IEEE BCTM 9.4, 1998, pp.164-167.
2	D. Knoll et al., "A flexible, low-cost, high performance SiGe:C BiCMOS process with a one-mask HBT module," IEEE, 2002.
3	B. Heinemann et al., "Novel collector design for high-speed SiGe:C HBTs," IEEE, 2002.
4	D. V. Singh et al., "Novel epitaxial p-Si/n-Si _{1-y} C _y /p-Si heterojunction bipolar transistors," IEEE, 2000.
5	B. El-Kareh et al., "A 5V complementary -SiGe BiCMOS technology for high-speed precision analog circuits."
6	D. V. Singh et al., "Effect of band alignment and density of states on the collector current in p-Si/n-Si _{1-y} C _y /p-Si HBTs," IEEE Transactions on Electron Devices, Vol. 50, No. 2, February 2003, pp. 425-32.

Examiner (To be assigned)

Date:

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EXAM. INITIAL		DOCUMENT NUMBER	DATE	INVENTOR/ASSIGNEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		2003/0219952	Nov. 27, 2003	<i>Fujimaki</i>			
		6,222,250	April 24, 2001	<i>Gomi</i>			
		4,719,185	Jan. 12, 1988	<i>Goth</i>			
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	7	Y. Chyan et al., "A 50-GHz 0.25 μ m implanted-base high-energy implanted-collector complementary modular BiCMOS (HEICBiC) technology for low-power wireless-communication VLSIs," IEEE BCTM 7.3, 1998, pp. 128-131.					
	8	D. L. Harame et al., "55 GHz polysilicon-emitter graded SiGe-base PNP transistors," 1991, p. 71.					
	9	T. Onai et al., "Self-aligned complementary bipolar technology for low-power dissipation and ultra-high-speed LSIs," IEEE Transactions on Electron Devices, Vol. 42, No. 3, March 1995, pp. 413-418.					
	10	S. J. Jeng et al., "A 210-GHz <i>f</i> _T SiGe HBT with a non-self-aligned structure," IEEE Electron Device Letters, Vol. 22, No. 11, November 2001.					
	11	J. D. Cressler et al., "A high-speed complementary silicon bipolar technology with 12-fJ power-delay product," IEEE Electron Device Letters, Vol. 14, No. 11, November 1993, pp. 523-526.					
	12	W. Klein et al., "75 GHz bipolar production technology for the 21st century," pp. 88-94.					
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